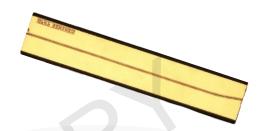
High Power RSOA Chip



Part Number: CHP-312

High Power RSOA Chip Single-Mode RSOA Curved Waveguide Wavelength at O band, 1310nm



Features

- 1mm RSOA Chip
- High Dynamic Range
- High Efficiency
- Standard RSOA Bare Die
- Cost Effective

Application

- Gain Element for External Cavity Laser
- Optical Communications
- LiDAR
- Free Space Communications
- Network Test Equipment



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

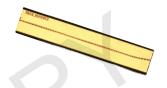
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High Power RSOA Chip



Specification

CHP-310



Optical	Symbol	Тур.	Units
Center Wavelength	λ_{C}	1310	nm
ASE Output Power @ 0.45A	Pout	6	mW
Aperture Width	AW	4	μm
Aperture Height	AH	1	μт
Spectral Width	Δλ	80	nm @ 3dB
Beam Exit Angle	θεχτ	19.5	Degree
Fast Axis Div.	ΘΤ	30	Deg FWHM
Slow Axis Div.	Θ∥	20	Deg FWHM
Front Facet Reflectivity		<0.1%	
Rear Face Reflectivity		98%	
Waveguide		Curved	
Electrical	Symbol		Units
Operating Current	lop	0.45	А
Operating Voltage	V _{op}	2	V
Mechanical		Range	Units
Chip Width		500	μm
Operating Temp.**		-20 to 75	°C
Storage Temp.		-40 to 85	°C

*Specified values are rated at a constant heat sink temperature of 20°C.

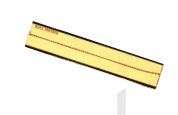
**High temperature operation will reduce performance and MTTF.

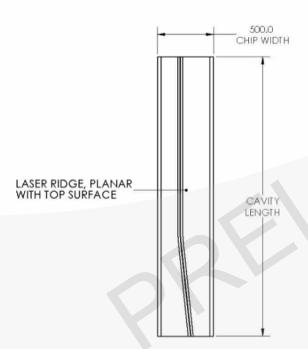
Unless otherwise indicated all values are nominal.

High Power RSOA Chip



Mechanical Drawing





CHIP ATTRIBUTES				
WAVELENGTH	1550nm ±20nm			
APERTURE WIDTH	4µm ±1µm			
CHIP WIDTH	0.500mm ±10µm			
THICKNESS	160µm±10µm			
CAVITY LENGTH	2.5mm ±10µm			

P-METAL				
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)		
Ti	50	±10		
Pt	125	±25		
Αu	250	±50		

N-METAL				
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)		
Ti	30	±10		
Pt	125	±25		
Αu	400	±40		

0.0 P-SIDE FULLY METALIZED SURFACE

160.0 N-SIDE FULLY METALIZED SURFACE

*Chip length of CHP-312 is 1mm & Wavelength is 1310nm. The diagram shown is for 2.5mm chip length with a wavelength of 1550nm.

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